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PATENT  
Attorney Docket No.: 02307Z-132710US  
Client Reference No.: 2003-144-2

On November 14, 2003

TOWNSEND and TOWNSEND and CREW LLP

By: Mark T. Davis

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of:

JULIN WAN, AMIYA K.  
MUKHERJEE, MATTHEW J.  
GASCH

Application No.: 10/658,126

Filed: September 8, 2003

For: SILICON NITRIDE/SILICON  
CARBIDE NANO-NANO  
COMPOSITES

Examiner: Not Yet Assigned

Art Unit: Not Yet Assigned

INFORMATION DISCLOSURE  
STATEMENT UNDER 37 CFR §1.97 and  
§1.98

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The references cited on attached form PTO/SB/08A and PTO/SB/08B are being called to the attention of the Examiner. Copies of the references are enclosed. It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR 1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is being made that a search has been conducted or that this statement encompasses all the possible relevant information.

JULIN WAN, AMIYA K. MUKHERJEE,  
MATTHEW J. GASCH  
Application No.: 10/658,126  
Page 2

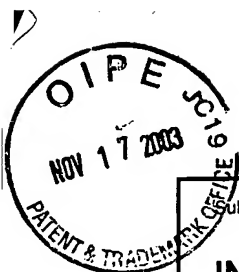
PATENT

Applicant believes that no fee is required for submission of this statement.  
However, if a fee is required, the Commissioner is authorized to deduct such fee from the undersigned's Deposit Account No. 20-1430. Please deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,

  
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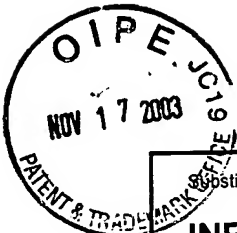
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	10/658,126		
		Filing Date	September 8, 2003		
		First Named Inventor	Wan, Julin		
		Art Unit	Not Yet Assigned		
		Examiner Name	Not Yet Assigned		
Sheet	1	of		Attorney Docket Number	02307Z-132710US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code <sup>2</sup> (if known)			
	AA	US-4,184,882	01-22-1980	Lange	
	AB	US-4,800,182	01-24-1989	Izaki et al.	
	AC	US-5,134,097	07-28-1992	Niihara et al.	
	AD	US-5,376,599	12-27-1994	Oshima et al.	
	AE	US-5,523,267	06-04-1996	Tanaka et al.	
	AF	US-5,541,143	07-30-1996	Hirosaki et al.	

FOREIGN PATENT DOCUMENTS										
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>			
		Country Code <sup>3</sup>	Number <sup>4</sup> Kind Code <sup>5</sup> (if known)							
NON PATENT LITERATURE DOCUMENTS										
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	AG	GASCH, Matthew J., et al.; "Creep of Silicon Nitride/Silicon Carbide Ceramic Nanocomposites"; <u>The Minerals, Metals &amp; Materials Society</u> 2002 pp. 247-256.								
	AH	GASCH, Matthew J., et al.; "Preparation of a Si <sub>3</sub> N <sub>4</sub> /SiC nanocomposite by high-pressure sintering of polymer precursor derived powders"; <u>Scripta Materialia</u> 2001 pp. 1063-1068 Vol. 45.								
	AI	NIIHARA, Koichi et al.; "Nanostructure and Thermomechanical Properties of Si <sub>3</sub> N <sub>4</sub> /SiC Composites Fabricated from Si-C-N Precursor Powders"; <u>J. Japan Soc. Powder and Powder Metall</u> 1989 pp. 169-172 Vol. 36.								
	AJ	RENDEL, Andreas et al.; "Silicon Nitride/Silicon Carbide Nanocomposite Materials: II, Hot Strength, Creep, and Oxidation Resistance"; <u>J. Am. Ceram. Soc.</u> 1998 pp. 1109-1120 Vol. 81 No. 5.								

Examiner Signature		Date Considered	
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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Kind Codes of U.S. Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.



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	AK	WAN, Julin et al.; "Consolidation and crystallization of Si <sub>3</sub> N <sub>4</sub> /SiC nanocomposites from a poly(urea-silazane) ceramic precursor"; <u>J. Mater. Res.</u> 2001 pp. 3274-3286 Vol. 16 No. 11		
	AL	WAN, Julin et al.; "In Situ Densification Behavior in the Pyrolysis Consolidation of Amorphous Si-N-C Bulk Ceramics from Polymer Precursors"; <u>J. Am. Ceram. Soc.</u> 2001 pp. 2165-2169 Vol. 84 No. 10.		
	AM	WAN, Julin et al.; "Processing and Properties of Ceramic Nanocomposites Produced from Polymer Precursor Pyrolysis, High Pressure Sintering and Spark Plasma Sintering"; <u>Mat. Res. Soc. Pro.</u> 2001 pp. B7.2.1-B7.2.5 Vol. 634.		
	AN	WAN, Julin et al.; "Effect of Ammonia Treatment on the Crystallization of Amorphous Silicon-Carbon-Nitrogen Ceramics Derived from Polymer Precursor Pyrolysis"; <u>J. Am. Ceram. Soc.</u> 2002 pp. 554-564 Vol. 85 No. 3.		
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	AP	WAN, Julin et al.; "The Creep Behavior of Si <sub>3</sub> N <sub>4</sub> /SiC Nanocomposites"; <u>JOM</u> 2003 pp. 28-33.		
	AQ	WAN, Julin et al.; "Silicon Nitride-Silicon Carbide Nanocomposites Fabricated by Electric-Field-Assisted Sintering"; <u>J. Am. Ceram. Soc.</u> 2003 pp. 526-528 Vol. 86 No. 3.		
	AR	WAN, Julin et al.; "Silicon Nitride/Silicon Carbide Nanocomposites from Polymer Precursor"; <u>Department of Chemical Engineering and Materials Science, University of California Davis</u> pp. 665-672.		

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